Shantou Huashan Electronic Devices Co.,Ltd.

PNP SILICON TRANSISTOR

HSBD440

APPLICATIONS

Medium Power Linear switching Applications

1—Emitter, E
2—Collector，C
3—Base，B

ABSOLUTE MAXIMUM RATINGS（T_a=25℃）

T_{stg}——Storage Temperature…… -55~150℃

T_j——Junction Temperature…… 150℃

P_C——Collector Dissipation（T_c=25℃）…… 36W

V_{CBO}——Collector-Base Voltage…… -60V

V_{CEO}——Collector-Emitter Voltage…… -60V

V_{CES}——Collector-Emitter Voltage…… -60V

V_{EBO}——Emitter-Base Voltage…… -5V

I_C——Collector Current(Pulse)…… -7A

I_C——Collector Current(DC)……- 4A

I_B——Base Current……-1A

ELECTRICAL CHARACTERISTICS（T_a=25℃）

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
I_{CBO}	Collector Cut-off Current			-100	μA	V_{CB}=-60V, I_E=0
I_{EBO}	Emitter Cut-off Current			-1	mA	V_{EB}=-5V, I_C=0
I_{CES}	Collector Cut-off Current			-100	μA	V_{CE}=-60V, V_{EB}=0
*H_{FE} (1)	DC Current Gain	20	140			V_{CE}=-5V, I_C=-10mA
*H_{FE} (2)	DC Current Gain	40	140			V_{CE}=-1V, I_C=-500mA
*H_{FE} (3)	DC Current Gain	25				V_{CE}=-1V, I_C=-2A
*$V_{CE(sat)}$	Collector- Emitter Saturation Voltage			-0.8	V	I_C=-2A, I_B=-0.2A
*$V_{BE(on1)}$	Base-Emitter On Voltage		-0.58		V	V_{CE}=-5V, I_C=-10mA
*$V_{BE(on2)}$	Base-Emitter On Voltage			-1.5	V	V_{CE}=-1V, I_C=-2A
$V_{CEO(sus)}$	Collector-Emitter Sustaining Voltage	-60			V	I_C=-100mA, I_B=0
ft	Current Gain-Bandwidth Product	3			MHz	V_{CE}=-1V, I_C=-250mA,

* Pulse Test:PW=300μS,Duty Cycle=1.5% Pulsed